

# High Voltage Power MOSFET

## IXTA02N250HV

$$V_{DSS} = 2500V$$

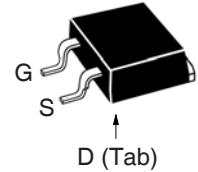
$$I_{D25} = 200mA$$

$$R_{DS(on)} \leq 450\Omega$$

N-Channel Enhancement Mode  
Fast Intrinsic Diode



TO-263AB



G = Gate      D = Drain  
S = Source    Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	2500	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GS} = 1M\Omega$	2500	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	200	mA
$I_{DM}$	$T_C = 25^\circ\text{C}$ , Pulse Width Limited by $T_{JM}$	600	mA
$P_D$	$T_C = 25^\circ\text{C}$	83	W
$T_J$		- 55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		- 55 ... +150	$^\circ\text{C}$
$T_L$	1.6mm (0.062 in.) from Case for 10s	300	$^\circ\text{C}$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ\text{C}$
$F_C$	Mounting Force	11..65 / 25..14.6	N/lb.
<b>Weight</b>		2.5	g

### Features

- High Voltage package
- High Blocking Voltage
- Fast Intrinsic Diode
- Low Package Inductance

### Advantages

- Easy to Mount
- Space Savings

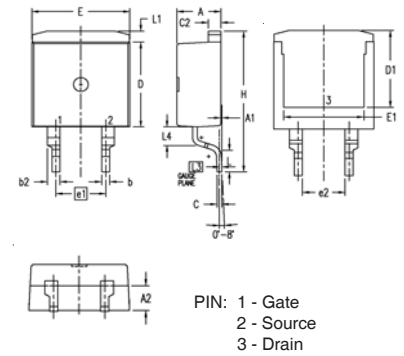
### Applications

- High Voltage Power Supplies
- Capacitor Discharge
- Pulse Circuits

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 250\mu\text{A}$	2500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\mu\text{A}$	2.5		4.5 V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = 0.8 \cdot V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			5 $\mu\text{A}$ 500 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 50mA$ , Note 1			450 $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 100\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1	88	145	mS
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		116	pF
$C_{oss}$			8	pF
$C_{rss}$			3	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 100\Omega$ (External)		19	ns
$t_r$			19	ns
$t_{d(off)}$			32	ns
$t_f$			33	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$		7.4	nC
$Q_{gs}$			0.7	nC
$Q_{gd}$			5.3	nC
$R_{thJC}$				1.5 $^\circ\text{C/W}$

### TO-263AB (VHV) Outline



SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.000	.008	0.00	0.20
A2	.091	.098	2.30	2.50
b	.028	.035	0.70	0.90
b2	.046	.054	1.18	1.38
C	.018	.024	0.45	0.60
C2	.049	.055	1.25	1.40
D	.354	.370	9.00	9.40
D1	.311	.327	7.90	8.30
E	.386	.402	9.80	10.20
E1	.307	.323	7.80	8.20
e1	.200 BSC		5.08 BSC	
(e2)	.163	.174	4.13	4.43
H	.591	.614	15.00	15.60
L	.079	.102	2.00	2.60
L1	.039	.055	1.00	1.40
L3	.010 BSC		0.254 BSC	
(L4)	.071	.087	1.80	2.20

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			200 mA
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			800 mA
$V_{SD}$	$I_F = 100\text{mA}$ , $V_{GS} = 0\text{V}$ , Note 1			2.0 V
$t_{rr}$	$I_F = 200\text{mA}$ , $-di/dt = 50\text{A}/\mu\text{s}$ , $V_R = 100\text{V}$		1.5	$\mu\text{s}$

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

\*Additional provisions for lead to lead voltage isolation are required at  $V_{DS} > 1200\text{V}$ .

### ADVANCE TECHNICAL INFORMATION

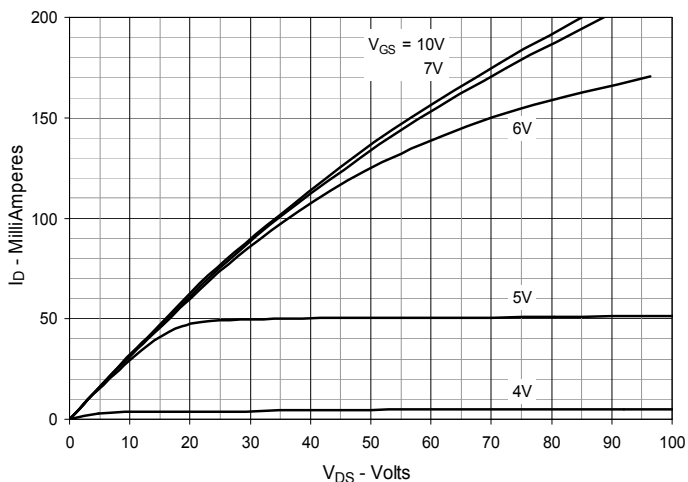
The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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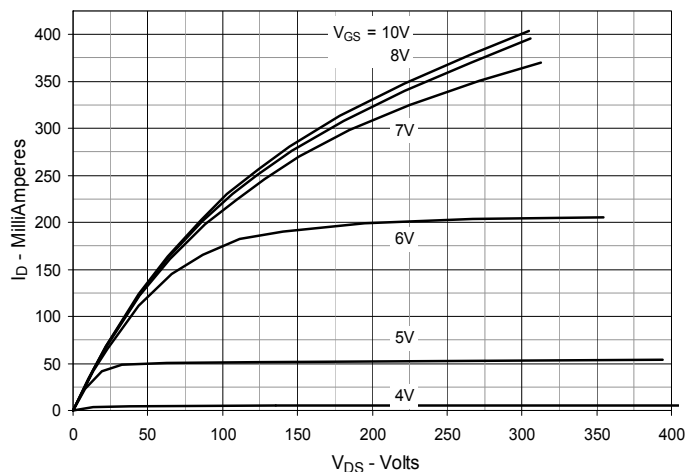
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

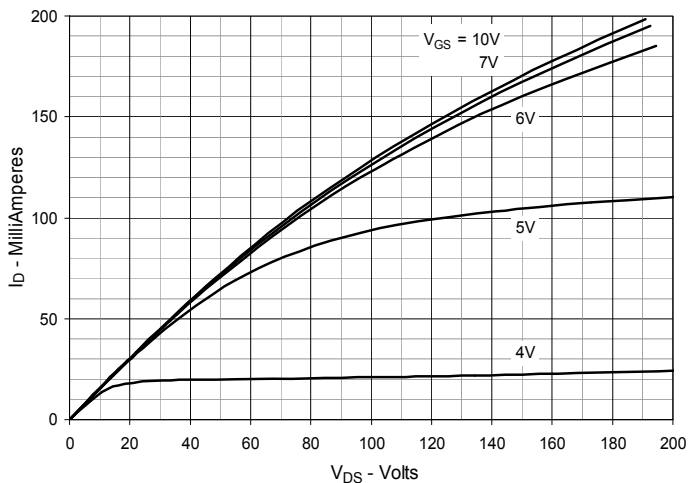
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



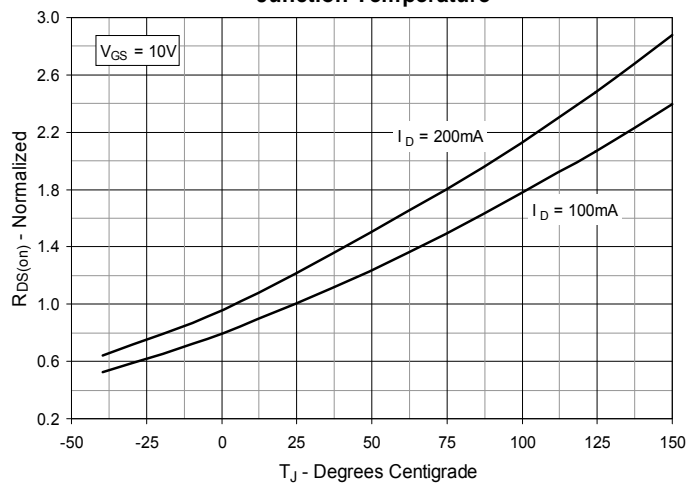
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



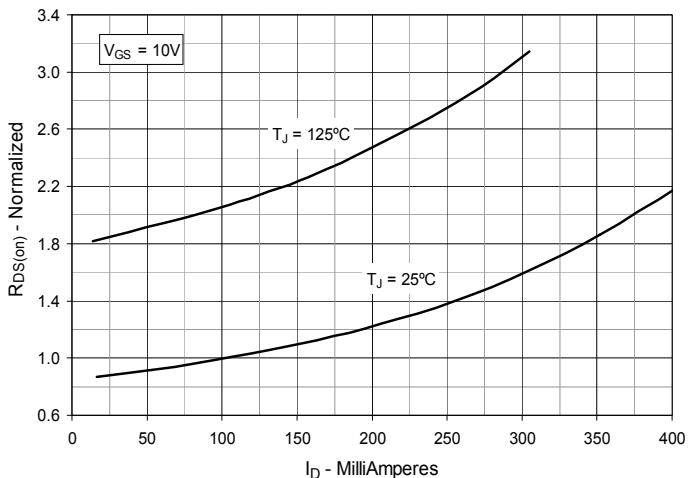
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



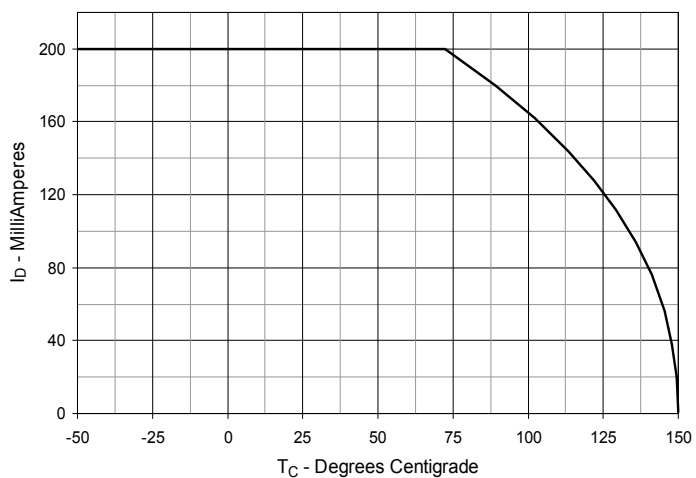
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 100\text{mA}$  Value vs. Junction Temperature**



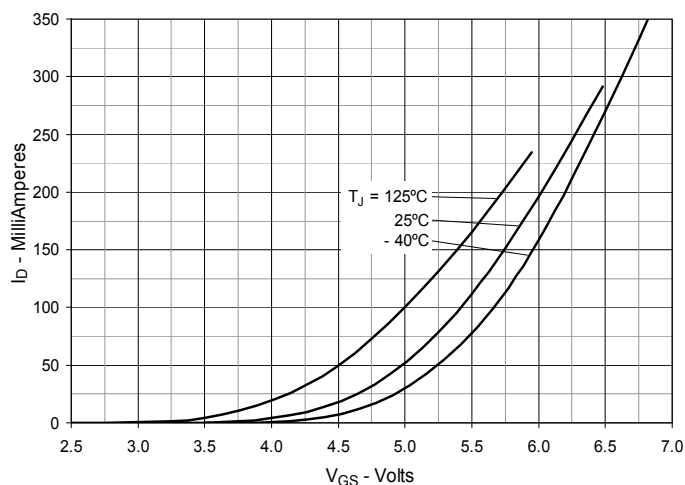
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 100\text{mA}$  Value vs. Drain Current**



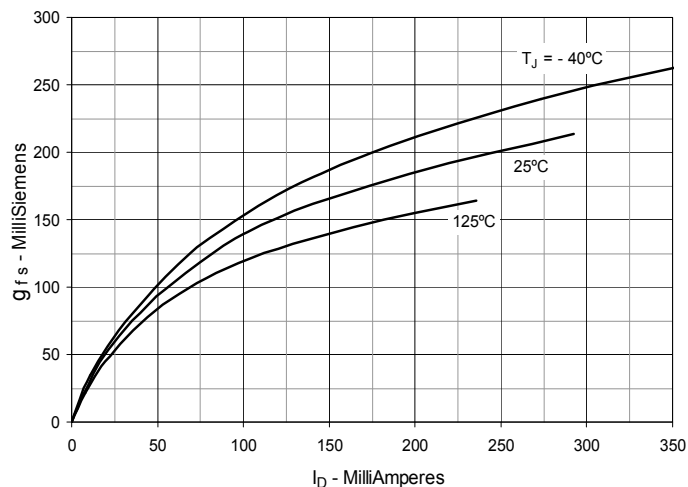
**Fig. 6. Maximum Drain Current vs. Case Temperature**



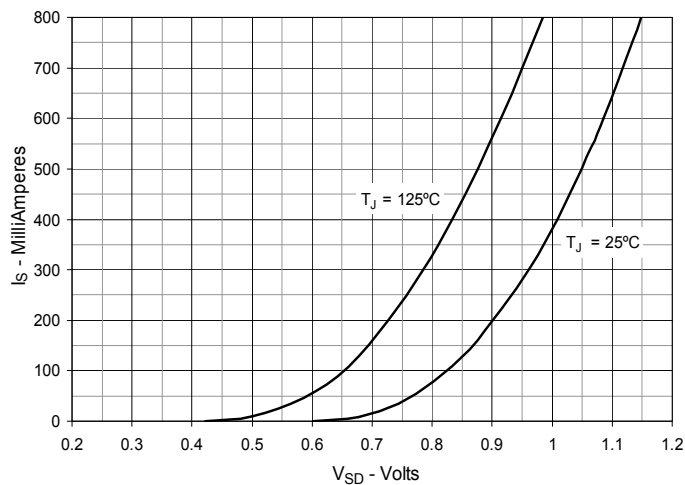
**Fig. 7. Input Admittance**



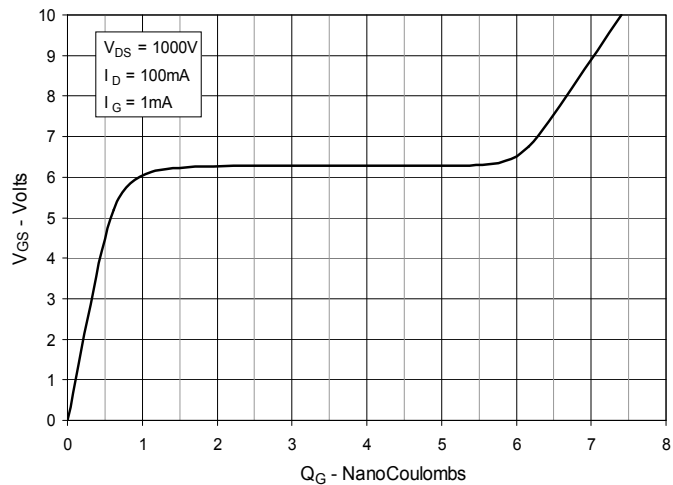
**Fig. 8. Transconductance**



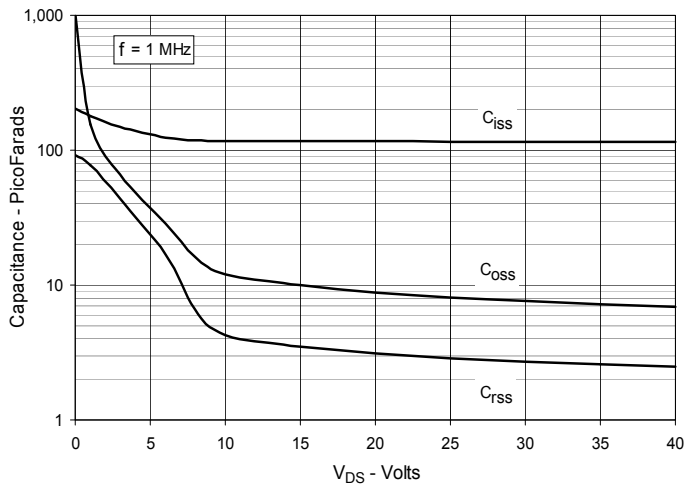
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



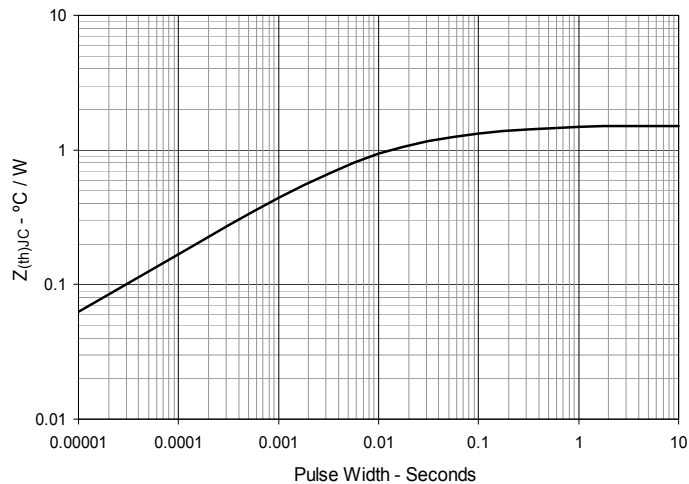
**Fig. 10. Gate Charge**



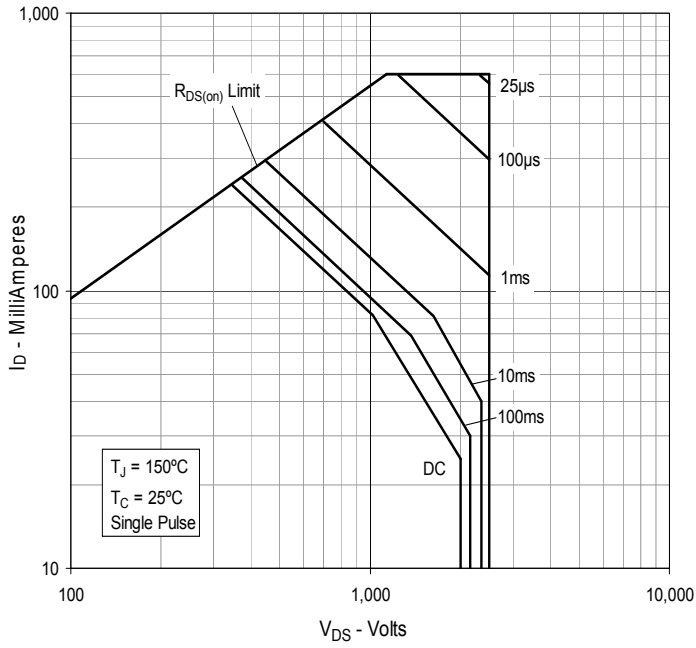
**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Impedance**



**Fig. 13. Forward-Bias Safe Operating Area**  
 @  $T_C = 25^\circ\text{C}$



**Fig. 14. Forward-Bias Safe Operating Area**  
 @  $T_C = 75^\circ\text{C}$

